

# PDTD143ET-Q

# 500 mA, 50 V NPN resistor-equipped transistor; R1 = 4.7 k $\Omega$ , R2 = 4.7 k $\Omega$

5 January 2022

**Product data sheet** 

# 1. General description

NPN Resistor-Equipped Transistor (RET) in a small SOT23 (TO-236AB) Surface-Mounted Device (SMD) plastic package.

PNP complement: PDTB143ET-Q

## 2. Features and benefits

- 500 mA output current capability
- · Built-in bias resistors
- · Simplifies circuit design
- · Reduces component count
- ± 10 % resistor ratio tolerance
- High temperature applications up to 175 °C
- Qualified according to AEC-Q101 and recommended for use in automotive applications

# 3. Applications

- IC inputs control
- · Cost-saving alternative to BC807 series transistors in digital applications
- Switching loads

## 4. Quick reference data

#### Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V <sub>CEO</sub>	collector-emitter voltage	open base		-	-	50	V
Io	output current			-	-	500	mA
R1	bias resistor 1		[1]	3.3	4.7	6.1	kΩ
R2/R1	bias resistor ratio		[1]	0.9	1	1.1	

[1] See "Section 11: Test information" for resistor calculation and test conditions.



500 mA, 50 V NPN resistor-equipped transistor; R1 = 4.7 k $\Omega$ , R2 = 4.7 k $\Omega$ 

# 5. Pinning information

## **Table 2. Pinning information**

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	I	input (base)	3	
2	GND	ground (emitter)		R1
3	0	output (collector)	SOT23	GND R2

# 6. Ordering information

## **Table 3. Ordering information**

Type number	Package					
	Name	Description	Version			
PDTD143ET-Q		plastic, surface-mounted package; 3 terminals; 1.9 mm pitch; 2.9 mm x 1.3 mm x 1 mm body	SOT23			

# 7. Marking

## Table 4. Marking codes

Type number	Marking code[1]
PDTD143ET-Q	%4Z

[1] % = placeholder for manufacturing site code

500 mA, 50 V NPN resistor-equipped transistor; R1 = 4.7 k $\Omega$ , R2 = 4.7 k $\Omega$ 

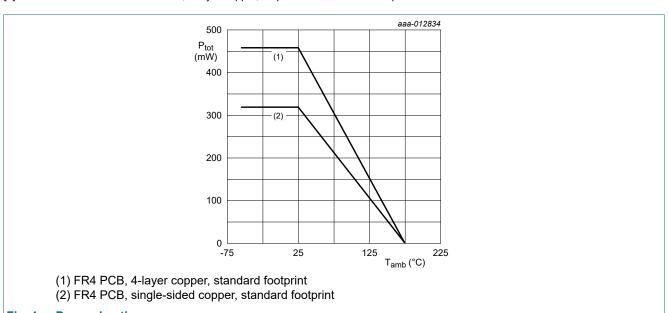
# 8. Limiting values

#### Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
$V_{CBO}$	collector-base voltage	open emitter		-	50	V
$V_{CEO}$	collector-emitter voltage	open base		-	50	V
$V_{EBO}$	emitter-base voltage	open collector		-	10	V
VI	input voltage	positive		-10	30	V
Io	output current			-	500	mA
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C	[1]	-	320	mW
			[2]	-	460	mW
Tj	junction temperature			-	175	°C
T <sub>amb</sub>	ambient temperature			-55	175	°C
T <sub>stg</sub>	storage temperature			-55	175	°C

- [1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided, 35 µm copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, 4-layer copper, tin-plated and standard footprint.



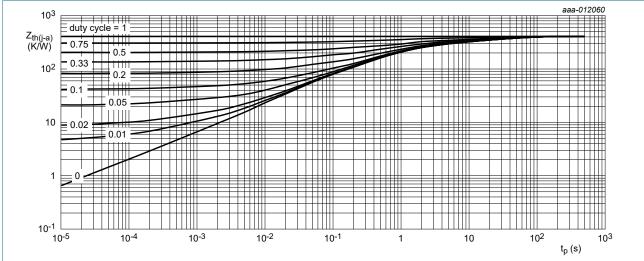
500 mA, 50 V NPN resistor-equipped transistor; R1 = 4.7 k $\Omega$ , R2 = 4.7 k $\Omega$ 

# 9. Thermal characteristics

**Table 6. Thermal characteristics** 

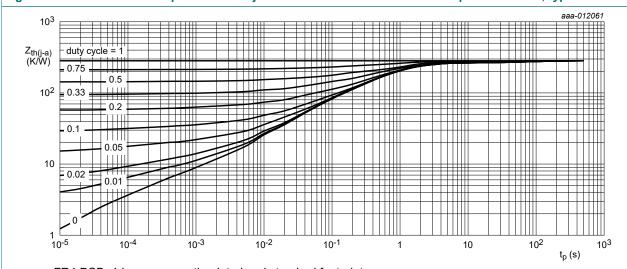
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
ui()-a)	thermal resistance from	in free air	[1]	-	-	470	K/W
	junction to ambient		[2]	-	-	327	K/W

- [1] Device mounted on an FR4 PCB, 35 µm copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, 4-layer copper, tin-plated and standard footprint.



FR4 PCB, single-sided 35 µm copper, tin-plated and standard footprint

Fig. 2. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



FR4 PCB, 4-layer copper, tin-plated and standard footprint

Fig. 3. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

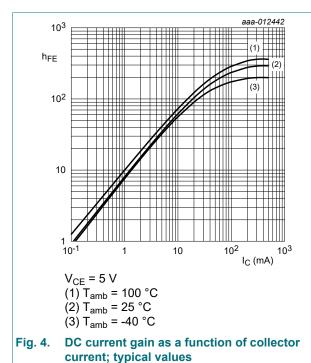
500 mA, 50 V NPN resistor-equipped transistor; R1 = 4.7 k $\Omega$ , R2 = 4.7 k $\Omega$ 

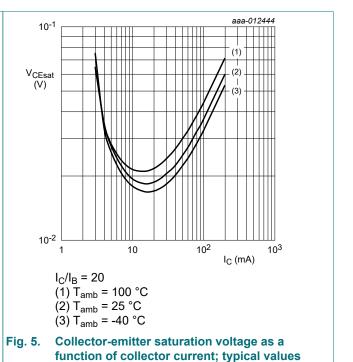
# 10. Characteristics

**Table 7. Characteristics** 

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
$V_{(BR)CBO}$	collector-base breakdown voltage	$I_C = 100 \ \mu A; I_E = 0 \ A; T_{amb} = 25 \ ^{\circ}C$		50	-	-	V
V <sub>(BR)CEO</sub>	collector-emitter breakdown voltage	$I_C = 2 \text{ mA}; I_B = 0 \text{ A}; T_{amb} = 25 ^{\circ}\text{C}$		50	-	-	V
I <sub>CBO</sub>	collector-base cut-off	V <sub>CB</sub> = 40 V; I <sub>E</sub> = 0 A; T <sub>amb</sub> = 25 °C		-	-	100	nA
	current	V <sub>CB</sub> = 50 V; I <sub>E</sub> = 0 A; T <sub>amb</sub> = 25 °C		-	-	100	nA
I <sub>CEO</sub>	collector-emitter cut-off current	V <sub>CE</sub> = 50 V; I <sub>B</sub> = 0 A; T <sub>amb</sub> = 25 °C		-	-	0.5	μΑ
I <sub>EBO</sub>	emitter-base cut-off current	$V_{EB} = 5 \text{ V}; I_{C} = 0 \text{ A}; T_{amb} = 25 ^{\circ}\text{C}$		-	-	0.9	mA
h <sub>FE</sub>	DC current gain	V <sub>CE</sub> = 5 V; I <sub>C</sub> = 50 mA; T <sub>amb</sub> = 25 °C		60	-	-	
V <sub>CEsat</sub>	collector-emitter saturation voltage	$I_C = 50 \text{ mA}; I_B = 2.5 \text{ mA}; T_{amb} = 25 ^{\circ}\text{C}$		-	-	100	mV
V <sub>I(off)</sub>	off-state input voltage	V <sub>CE</sub> = 5 V; I <sub>C</sub> = 100 μA; T <sub>amb</sub> = 25 °C		0.6	0.9	1.5	V
V <sub>I(on)</sub>	on-state input voltage	V <sub>CE</sub> = 0.3 V; I <sub>C</sub> = 20 mA; T <sub>amb</sub> = 25 °C		1	1.6	2.2	V
R1	bias resistor 1		[1]	3.3	4.7	6.1	kΩ
R2/R1	bias resistor ratio		[1]	0.9	1	1.1	
C <sub>c</sub>	collector capacitance	$V_{CB}$ = 10 V; $I_{E}$ = 0 A; $i_{e}$ = 0 A; f = 1 MHz; $T_{amb}$ = 25 °C		-	7	-	pF
f <sub>T</sub>	transition frequency	$V_{CE}$ = 5 V; $I_{C}$ = 50 mA; f = 100 MHz; $T_{amb}$ = 25 °C	[2]	-	225	-	MHz

- [1] See "Section 11: Test information" for resistor calculation and test conditions.
- [2] Characteristics of built-in transistor.





### 500 mA, 50 V NPN resistor-equipped transistor; R1 = 4.7 k $\Omega$ , R2 = 4.7 k $\Omega$

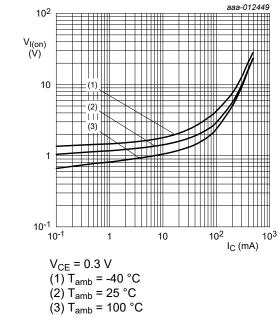
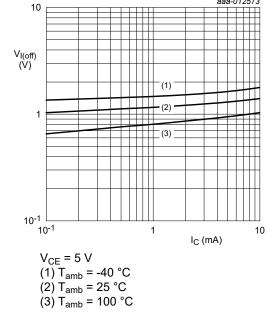
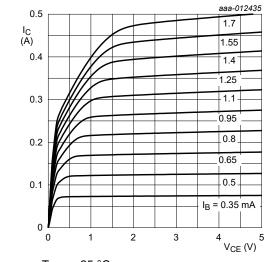


Fig. 6. On-state input voltage as a function of collector | Fig. 7. current; typical values

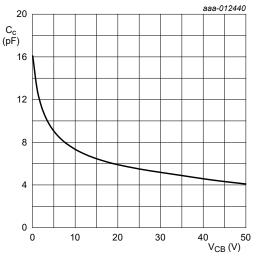


Off-state input voltage as a function of collector current; typical values



T<sub>amb</sub> = 25 °C

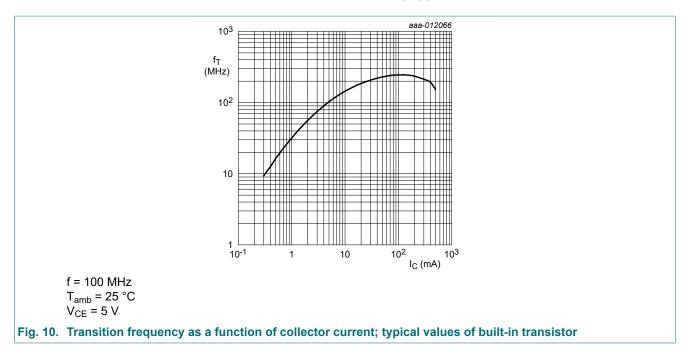
Fig. 8. Collector current as a function of collectoremitter voltage; typical values



f = 1 MHzT<sub>amb</sub> = 25 °C

Fig. 9. Collector capacitance as a function of collectorbase voltage; typical values

# 500 mA, 50 V NPN resistor-equipped transistor; R1 = 4.7 k $\Omega$ , R2 = 4.7 k $\Omega$



500 mA, 50 V NPN resistor-equipped transistor; R1 = 4.7 k $\Omega$ , R2 = 4.7 k $\Omega$ 

# 11. Test information

#### **Quality information**

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - Stress test qualification for discrete semiconductors, and is suitable for use in automotive applications.

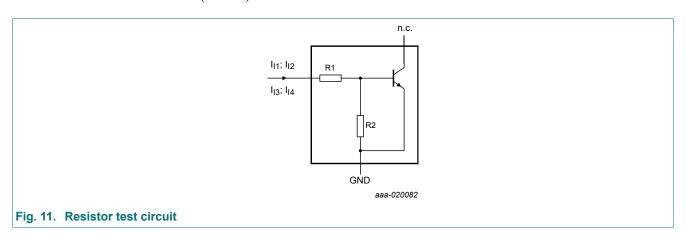
#### **Resistor calculation**

Calculation of bias resistor 1 (R1)

$$R1 = \frac{V(I12) - V(I11)}{I12 - I11}$$

· Calculation of bias resistor ratio (R2/R1)

$$\frac{R2}{R1} = \frac{V(I14) - V(I13)}{R1 \cdot (I14 - I13)} - 1$$



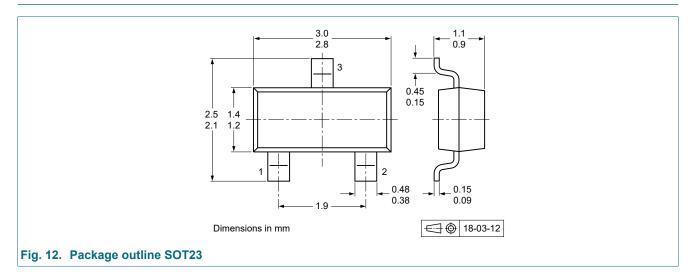
#### **Resistor test conditions**

**Table 8. Resistor test conditions** 

R1 (kΩ)	R2 (kΩ)	Test conditions				
		I <sub>11</sub>	I <sub>12</sub>	I <sub>13</sub>	I <sub>14</sub>	
4.7	4.7	1.3 mA	1.5 mA	-1.05 mA	-1.25 mA	

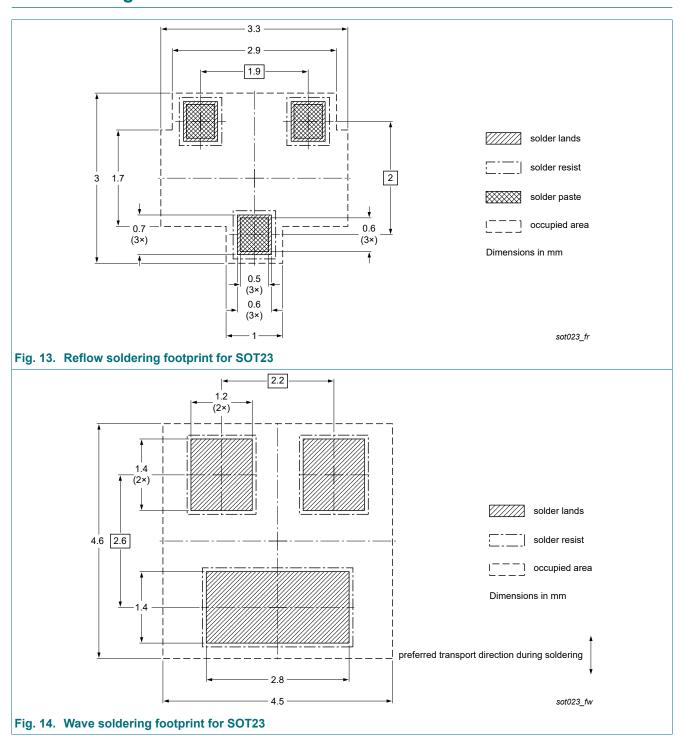
500 mA, 50 V NPN resistor-equipped transistor; R1 = 4.7 k $\Omega$ , R2 = 4.7 k $\Omega$ 

# 12. Package outline



500 mA, 50 V NPN resistor-equipped transistor; R1 = 4.7 k $\Omega$ , R2 = 4.7 k $\Omega$ 

# 13. Soldering



500 mA, 50 V NPN resistor-equipped transistor; R1 = 4.7 k $\Omega$ , R2 = 4.7 k $\Omega$ 

# 14. Revision history

## Table 9. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PDTD143ET-Q v.1	20220105	Product data sheet	-	-

#### 500 mA, 50 V NPN resistor-equipped transistor; R1 = 4.7 k $\Omega$ , R2 = 4.7 k $\Omega$

# 15. Legal information

#### **Data sheet status**

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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